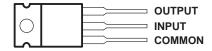
- 3-Terminal Regulators
- Output Current Up to 1.5 A
- No External Components
- Internal Thermal Overload Protection
- High-Power Dissipation Capability
- Internal Short-Circuit Current Limiting
- Output Transistor Safe-Area Compensation
- Essentially Equivalent to National LM320 Series

description

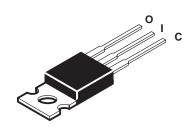
This series of fixed-negative-voltage monolithic integrated-circuit voltage regulators is designed to complement Series $\mu A7800$ in a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 1.5 A of output current. The internal current limiting and thermal shutdown features of these regulators make them essentially immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents and also as the power pass element in precision regulators.

KC PACKAGE (TOP VIEW)

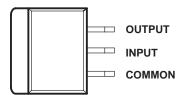


The input terminal is in electrical contact with the mounting base

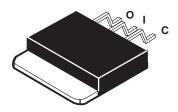
TO-220AB



KTE PACKAGE (TOP VIEW)



The input terminal is in electrical contact with the mounting base.



AVAILABLE OPTIONS

	PACKAGED DEVICES			
TA	(V) (V)	HEAT-SINK MOUNTED (KC)	HEAT-SINK MOUNTED _† (KTE)	FORM (Y)
	-5	μA7905CKC	μΑ7905CKTE	μΑ7905Υ
	-5.2	μΑ7952CKC	μΑ7952CKTE	μΑ7952Y
	-6	μΑ7906CKC	μΑ7906CKTE	μΑ7906Υ
0°C to 125°C	-8	μΑ7908CKC	μΑ7908CKTE	μΑ7908Υ
0 0 10 125 0	-12	μΑ7912CKC	μΑ7912CKTE	μΑ7912Y
	-15	μΑ7915CKC	μΑ7915CKTE	μΑ7915Y
	-18	μΑ7918CKC	μΑ7918CKTE	μΑ7918Υ
	-24	μΑ7924CKC	μΑ7924CKTE	μΑ7924Υ

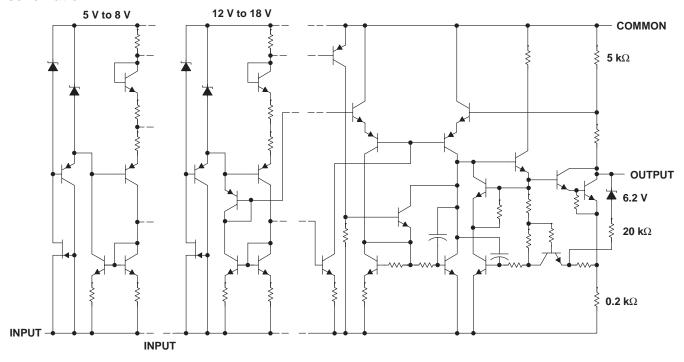
 $[\]ensuremath{^{\dagger}}$ The KTE package is also available taped and reeled.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



schematic



All component values are nominal.

absolute maximum ratings over operating temperature range (unless otherwise noted)

Input voltage, V _I : μA7924C–40 \
All others
Continuous total power dissipation at (or below): T _A = 25°C (see Note 1) See Dissipation Rating Tables
T _C = 90°C (see Note 1) See Dissipation Rating Tables
Operating free-air, T _A , case, T _C , or virtual junction, T _J , temperature range 0 to 150°C
Storage temperature range, T _{stq} –65 to 150°C
Lead temperature 3.2 mm (1/8 inch) from case for 10 seconds

NOTE 1: For operation above 25°C free-air or 90°C case temperature, refer to Figures 1 and 2. To avoid exceeding the design maximum virtual junction temperature, these ratings should not be exceeded. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal overload protection may be activated at power levels slightly above or below the rated dissipation.

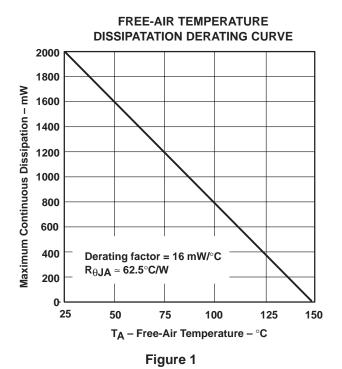
DISSIPATION RATING TABLE — FREE-AIR TEMPERATURE

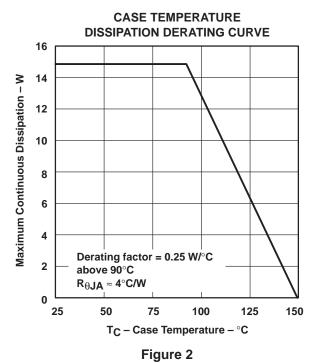
PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 105°C POWER RATING	T _A = 125°C POWER RATING
KC	2000 mW	16.0 mW/°C	1280 mW	720 mW	400 mW
KTE	1900 mW	15.2 mW/°C	1216 mW	684 mW	380 mW

DISSIPATION RATING TABLE — CASE TEMPERATURE

$\begin{array}{cc} \text{PACKAGE} & \text{$T_{\text{C}} \leq 90^{\circ}\text{C}$} \\ \text{POWER RATING} \end{array}$		DERATING FACTOR ABOVE T _C = 90°C	T _A = 125°C POWER RATING
KC	15000 mW	250.0 mW/°C	6250 mW
KTE	14300 mW	238.0 mW/°C	5970 mW







recommended operating conditions

		MIN	MAX	UNIT
	μΑ7905C	-7	-25	
	μA7952C	-7.2	-25	
	μA7906C	-8	-25	
Input voltage, V _I Output current, IO	μA7908C	-10.5	-25	V
input voitage, vi	μA7912C	-14.5	-30	V
μΑ7905C	μA7915C	-17.5	-30	
	-33			
	μA7924C	-27	-28	
Output current, IO			1.5	Α
Operating virtual junction temperature, T ₁		0	125	°C

electrical characteristics at specified virtual junction temperature, $V_I = -10~V,\,I_O = 500~mA$ (unless otherwise noted)

DADAMETED	TEST COMPITIONS	- +	μ Α7905C			UNITS
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIIS
		25°C	-4.8	-5	-5.2	
Output voltage [‡]	I_{O} = 5 mA to 1 A, P \leq 15 W V_{I} = -7 V to -20 V,	0°C to 125°C	-4.75		-5.25	V
Input regulation	$V_{ } = -7 \text{ V to } -25 \text{ V}$			12.5	50	mV
Input regulation	$V_{ } = -8 \text{ V to } -12 \text{ V}$	1		4	15	IIIV
Ripple rejection	$V_1 = -8 \text{ V to } -18 \text{ V}, \qquad f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Output regulation	I _O = 5 mA to 1.5 A			15	100	mV
Output regulation	I _O = 250 mA to 750 mA	1		5	50	IIIV
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-0.4		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		125		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		1.5	2	mA
Bias current change	V _I = -7 V to -25 V			0.15	0.5	A
	I _O = 5 mA to 1 A	1		0.08	0.5	mA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = -10 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.+	μ	UNITS		
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	UNITS
		25°C	-5	-5.2	-5.4	
Output voltage [‡]	I_{O} = 5 mA to 1 A, P \leq 15 W V_{I} = -7.2 V to -20 V,	0°C to 125°C	-4.95		-5.45	V
Innut regulation	$V_{I} = -7.2 \text{ V to } -25 \text{ V}$			12.5	100	mV
Input regulation	$V_{I} = -8.2 \text{ V to } -12 \text{ V}$	1		4	50	IIIV
Ripple rejection	$V_1 = -8.2 \text{ V to } -18 \text{ V}, f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Outrout no mulation	I _O = 5 mA to 1.5 A			15	100	\/
Output regulation	I _O = 250 mA to 750 mA	1		5	50	mV
Temperature coefficient of output voltage	$I_O = 5 \text{ mA}$	0°C to 125°C		-0.4		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		125		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		1.5	2	mA
Dies surrent shangs	$V_1 = -7.2 \text{ V to } -25 \text{ V}$			0.15	1.3	mA
Bias current change	I _O = 5 mA to 1 A]		0.08	0.5	IIIA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.



electrical characteristics at specified virtual junction temperature, $V_I = -11 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.†	μ Α7906C			UNITS
I ANAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIIS
		25°C	-5.75	-6	-6.25	
Output voltage‡	$I_{O} = 5 \text{ mA to 1 A}, \qquad V_{I} = -8 \text{ V to } -21 \text{ V}, \\ P \le 15 \text{ W}$	0°C to 125°C	-5.7		-6.3	V
land a sudation	$V_{I} = -8 \text{ V to } -25 \text{ V}$			12.5	120	\/
Input regulation	$V_{I} = -9 \text{ V to } -13 \text{ V}$	1		4	60	mV
Ripple rejection	$V_I = -9 \text{ V to } -19 \text{ V}, \qquad f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Output as audation	I _O = 5 mA to 1.5 A			15	120	\/
Output regulation	I _O = 250 mA to 750 mA	1		5	60	mV
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-0.4		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		150		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		1.5	2	mA
Bias current change	V _I = −8 V to −25 V			0.15	1.3	A
	I _O = 5 mA to 1 A	1		0.08	0.5	mA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = -14 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.:t	μ Α7908C			UNITS
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNITS
		25°C	-7.7	-8	-8.3	
Output voltage [‡]	$I_O = 5$ mA to 1 A, $V_I = -10.5$ V to -23 V, $P \le 15$ W	0°C to 125°C	-7.6		-8.4	V
land an adding	$V_{I} = -10.5 \text{ V to } -25 \text{ V}$ 12.5 160	\/				
Input regulation	V _I = -11 V to -17 V	1		4	80	mV
Ripple rejection	$V_I = -11.5 \text{ V to } -21.5 \text{ V}, f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Output no mulation	I _O = 5 mA to 1.5 A			15	160	mV
Output regulation	I _O = 250 mA to 750 mA	1		5	80	IIIV
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-0.6		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		200		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		1.5	2	mA
Bias current change	$V_{\parallel} = -10.5 \text{ V to } -25 \text{ V}$			0.15	1	A
	I _O = 5 mA to 1 A]		0.08	0.5	mA
Peak output current		25°C		2.1		А

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.



electrical characteristics at specified virtual junction temperature, $V_I = -19~V,\,I_O = 500~mA$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	- +	μ	UNITS		
TANAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIIS
		25°C	-11.5	-12	-12.5	
Output voltage‡	I_{O} = 5 mA to 1 A, V_{I} = -14.5 V to -27 V, $P \le$ 15 W	0°C to 125°C	-11.4		-12.6	V
logue regulation	$V_{I} = -14.5 \text{ V to } -30 \text{ V}$			5	80	mV
Input regulation	$V_{ } = -16 \text{ V to } -22 \text{ V}$	1		3	30	IIIV
Ripple rejection	$V_I = -15 \text{ V to } -25 \text{ V}, f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Output regulation	I _O = 5 mA to 1.5 A			15	200	mV
Output regulation	I _O = 250 mA to 750 mA	1		5	75	IIIV
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-0.8		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		300		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		2	3	mA
Dies surrent shangs	$V_{I} = -14.5 \text{ V to } -30 \text{ V}$			0.04	0.5	A
Bias current change	I _O = 5 mA to 1 A]		0.06	0.5	mA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = -23 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.:t	μ	UNITS		
PARAMETER		T _J †	MIN	TYP	MAX	UNITS
		25°C	-14.4	-15	-15.6	
	I_O = 5 mA to 1 A, V_I = -17.5 V to -30 V, $P \le 15$ W	0°C to 125°C	-14.25		-15.75	V
lanut regulation	$V_{I} = -17.5 \text{ V to } -30 \text{ V}$			5	100	\/
Input regulation	$V_{I} = -20 \text{ V to } -26 \text{ V}$]		3	50	mV
Ripple rejection	$V_1 = -18.5 \text{ V to } -28.5 \text{ V}, f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Outrout no mulation	I _O = 5 mA to 1.5 A			20	300	\/
Output regulation	I _O = 250 mA to 750 mA	1		8	150	mV
Temperature coefficient of output voltage	$I_O = 5 \text{ mA}$	0°C to 125°C		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		375		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		2	3	mA
Bias current change	$V_{I} = -17.5 \text{ V to } -30 \text{ V}$			0.04	0.5	A
	I _O = 5 mA to 1 A			0.06	0.5	mA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.



electrical characteristics at specified virtual junction temperature, $V_I = -27 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.†	μ Α7918C			UNITS
FARAIVIETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNITS
		25°C	-17.3	-18	-18.7	
	$I_O = 5$ mA to 1 A, $V_I = -21$ V to -33 V, $P \le 15$ W	0°C to 125°C	-17.1		-18.9	V
land an addition	$V_{\parallel} = -21 \text{ V to } -33 \text{ V}$			5	360	\/
Input regulation	$V_{ } = -24 \text{ V to } -30 \text{ V}$	1		3	180	mV
Ripple rejection	$V_{\parallel} = -22 \text{ V to } -32 \text{ V}, f = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Outrot as relation	I _O = 5 mA to 1.5 A			30	360	\/
Output regulation	I _O = 250 mA to 750 mA	1		10	180	mV
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		450		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		2	3	mA
Bias current change	V _I = −21 V to −33 V			0.04	1	A
	I _O = 5 mA to 1 A	1		0.06	0.5	mA
Peak output current		25°C		2.1		А

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = -33 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T _J †	μ Α7924C			UNITS
			MIN	TYP	MAX	UNITS
Output voltage [‡]		25°C	-23	-24	-25	· V
	I_O = 5 mA to 1 A, V_I = -27 V to -38 V, $P \le 15$ W	0°C to 125°C	-22.8		-25.2	
Input regulation	$V_{I} = -27 \text{ V to } -38 \text{ V}$			5	480	mV
	$V_{I} = -30 \text{ V to } -36 \text{ V}$	1		3	240	
Ripple rejection	$V_1 = -28 \text{ V to } -38 \text{ V}, \text{ f} = 120 \text{ Hz}$	0°C to 125°C	54	60		dB
Output regulation	I _O = 5 mA to 1.5 A			85	480	mV
	I _O = 250 mA to 750 mA	1		25	240	
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		600		μV
Dropout voltage	I _O = 1 A	25°C		1.1		V
Bias current		25°C		2	3	mA
Bias current change	V _I = −27 V to −38 V			0.04	1	mA
	I _O = 5 mA to 1 A]		0.06	0.5	
Peak output current		25°C		2.1		А

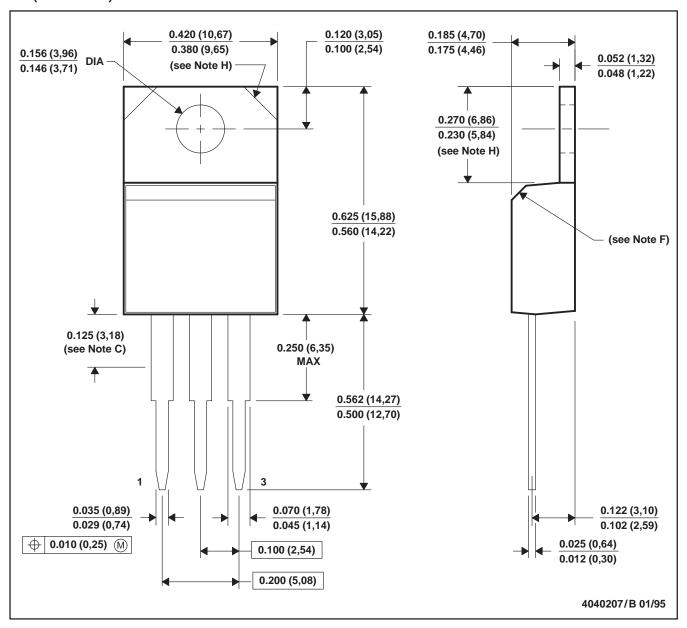
[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 2-μF capacitor across the input and a 1-μF capacitor across the output. ‡ This specification applies only for dc power dissipation permitted by absolute maximum ratings.



MECHANICAL INFORMATION

KC (R-PSFM-T3)

PLASTIC FLANGE-MOUNT PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

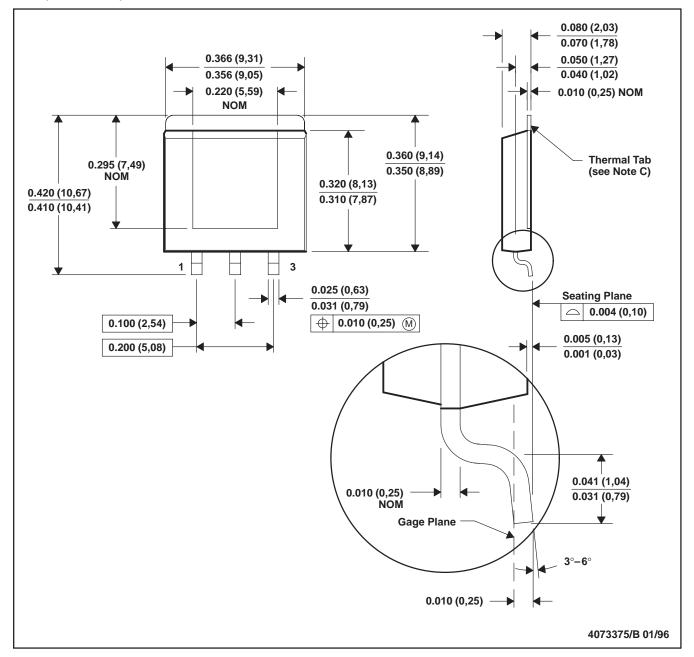
- B. This drawing is subject to change without notice.
- C. Lead dimensions are not controlled within this area.
- D. All lead dimensions apply before solder dip.
- E. The center lead is in electrical contact with the mounting tab.
- F. The chamfer is optional.
- G. Falls within JEDEC TO-220AB
- H. Tab contour optional within these dimensions



MECHANICAL INFORMATION

KTE (R-PSFM-T3)

PLASTIC FLANGE-MOUNT PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. The center lead is in electrical contact with the thermal tab.

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